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NX3008PBK

30 V, 230 mA P-channel Trench MOSFET Rev. 1 — 1 August 2011

Product data sheet

Product profile

1.1 General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

1.2 Features and benefits

- Very fast switching
- Low threshold voltage
- Trench MOSFET technology
- ESD protection up to 2 kV
- AEC-Q101 qualified

1.3 Applications

- Relay driver
- High-speed line driver

- High-side loadswitch
- Switching circuits

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j = 25 °C	-	-	-30	V
V_{GS}	gate-source voltage		-8	-	8	V
I_D	drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C}$	<u>[1]</u> _	-	-230	mA
Static characteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = -4.5 \text{ V};$ $I_D = -200 \text{ mA}; T_j = 25 \text{ °C}$	-	2.8	4.1	Ω

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



30 V, 230 mA P-channel Trench MOSFET

017aaa259

2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	S	source	3	D
3	D	drain	1	G

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
NX3008PBK	TO-236AB	plastic surface-mounted package; 3 leads	SOT23

4. Marking

Table 4. Marking codes

Type number	Marking code ^[1]
NX3008PBK	KT%

^[1] % = placeholder for manufacturing site code.

30 V, 230 mA P-channel Trench MOSFET

5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Parameter	Conditions	Mi	n Max	Unit
drain-source voltage	T _j = 25 °C	-	-30	V
gate-source voltage		-8	8	V
drain current	$V_{GS} = -4.5 \text{ V}; T_{amb} = 25 \text{ °C}$	<u>[1]</u> -	-230	mA
	$V_{GS} = -4.5 \text{ V}; T_{amb} = 100 \text{ °C}$	<u>[1]</u> -	-145	mA
peak drain current	$T_{amb} = 25 \text{ °C}$; single pulse; $t_p \le 10 \mu\text{s}$	-	-1	Α
total power dissipation	T _{amb} = 25 °C	[2] _	350	mW
		<u>[1]</u> _	420	mW
	$T_{sp} = 25 ^{\circ}C$	-	1140	mW
junction temperature		-55	5 150	°C
ambient temperature		-55	5 150	°C
storage temperature		-65	5 150	°C
diode				
source current	T _{amb} = 25 °C	<u>[1]</u> _	-230	mA
n rating				
electrostatic discharge voltage	НВМ	[3] _	2000	V
	drain-source voltage gate-source voltage drain current peak drain current total power dissipation junction temperature ambient temperature storage temperature diode source current rating	$ \begin{array}{lll} drain\text{-source voltage} & T_j = 25 ^\circ\text{C} \\ gate\text{-source voltage} \\ drain current & V_{GS} = -4.5 \text{V}; T_{amb} = 25 ^\circ\text{C} \\ \hline V_{GS} = -4.5 \text{V}; T_{amb} = 100 ^\circ\text{C} \\ \hline peak drain current & T_{amb} = 25 ^\circ\text{C}; single pulse; t_p \leq 10 \mu\text{s} \\ \hline total power dissipation & T_{amb} = 25 ^\circ\text{C} \\ \hline Junction temperature & \\ ambient temperature & \\ storage temperature & \\ \hline storage temperature & \\ \hline source current & T_{amb} = 25 ^\circ\text{C} \\ \hline 1 rating & \\ \hline \end{array} $	$ \begin{array}{c} drain\text{-source voltage} \\ gate\text{-source voltage} \\ drain current \\ \hline \\ V_{GS} = -4.5 \text{ V}; T_{amb} = 25 ^{\circ}\text{C} \\ \hline \\ V_{GS} = -4.5 \text{ V}; T_{amb} = 100 ^{\circ}\text{C} \\ \hline \\ 11 \\ - \\ \hline \\ peak drain current \\ \hline \\ total power dissipation \\ \hline \\ T_{amb} = 25 ^{\circ}\text{C}; single pulse; t_p \leq 10 \mus \\ \hline \\ T_{amb} = 25 ^{\circ}\text{C} \\ \hline \\ 11 \\ - \\ \hline \\ T_{sp} = 25 ^{\circ}\text{C} \\ \hline \\ junction temperature \\ \hline \\ ambient temperature \\ \hline \\ storage temperature \\ \hline \\ storage temperature \\ \hline \\ \\ source current \\ \hline \\ T_{amb} = 25 ^{\circ}\text{C} \\ \hline \\ 11 \\ - \\ \hline \\ T_{amb} = 25 ^{\circ}\text{C} \\ \hline \\ \\ \hline \\ 11 \\ - \\ \hline \\ \\ \hline \\ \\ \hline \\ \\ \\ \\ \\ \\ \\ \\ \\ \\$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

^[2] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[3] Measured between all pins.

30 V, 230 mA P-channel Trench MOSFET

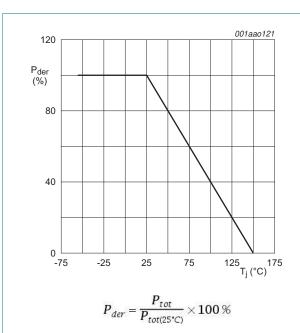


Fig 1. Normalized total power dissipation as a function of junction temperature

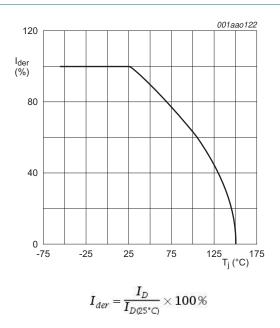
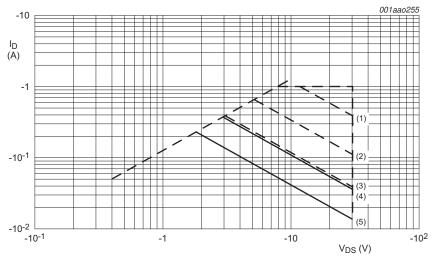


Fig 2. Normalized continuous drain current as a function of junction temperature



I_{DM} is a single pulse

- (1) $t_p = 1 \text{ ms}$
- (2) $t_p = 10 \text{ ms}$
- (3) $t_p = 100 \text{ ms}$
- (4) DC; $T_{sp} = 25 \, ^{\circ}\text{C}$
- (5) DC; T_{amb} = 25 °C; 1 cm² drain mounting pad

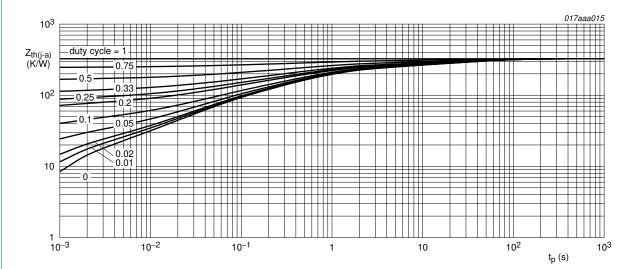
Fig 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	<u>[1]</u> -	310	370	K/W
			[2] _	260	300	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point		-	-	115	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².



FR4 PCB, standard footprint

Fig 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

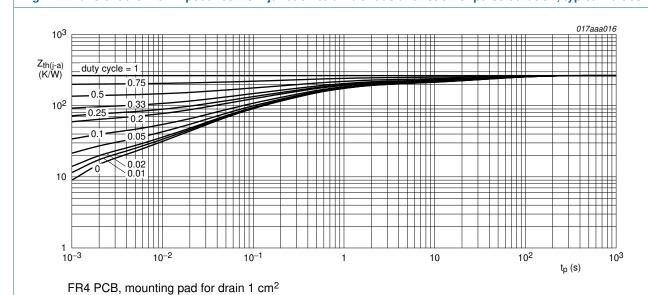


Fig 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

30 V, 230 mA P-channel Trench MOSFET

7. Characteristics

Table 7. Characteristics

Characteristics					
Parameter	Conditions	Min	Тур	Max	Unit
aracteristics					
drain-source breakdown voltage	$I_D = -250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$	-30	-	-	V
gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.6	-0.9	-1.1	V
drain leakage current	$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 150 \text{ °C}$	-	-	-10	μΑ
	$V_{DS} = -30 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-	-1	μΑ
gate leakage current	$V_{GS} = 8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-0.2	-1	μΑ
	$V_{GS} = -8 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-0.2	-1	μΑ
	$V_{GS} = 4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-10	-	nA
	$V_{GS} = -4.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-10	-	nA
	$V_{GS} = 2.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-1	-	nA
	$V_{GS} = -2.5 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-	-1	-	nA
drain-source on-state	$V_{GS} = -4.5 \text{ V}; I_D = -200 \text{ mA}; T_j = 25 \text{ °C}$	-	2.8	4.1	Ω
resistance	$V_{GS} = -4.5 \text{ V}; I_D = -200 \text{ mA}; T_j = 150 \text{ °C}$	-	5.3	7.8	Ω
	$V_{GS} = -2.5 \text{ V}; I_D = -10 \text{ mA}; T_j = 25 \text{ °C}$	-	5.3	6.5	Ω
forward transconductance	$V_{DS} = -10 \text{ V}; I_D = -200 \text{ mA}; T_j = 25 \text{ °C}$	-	160	-	mS
characteristics					
total gate charge	$V_{DS} = -15 \text{ V}; I_D = -200 \text{ mA};$	-	0.55	0.72	nC
gate-source charge	$V_{GS} = -4.5 \text{ V}; T_j = 25 \text{ °C}$	-	0.23	-	nC
gate-drain charge		-	0.09	-	nC
input capacitance	$V_{DS} = -15 \text{ V}; f = 1 \text{ MHz}; V_{GS} = 0 \text{ V};$	-	31	46	pF
output capacitance	T _j = 25 °C	-	6.5	-	pF
reverse transfer capacitance		-	2.3	-	pF
turn-on delay time	$V_{DS} = -20 \text{ V}; R_L = 250 \Omega; V_{GS} = -4.5 \text{ V};$	-	19	38	ns
rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	30	-	ns
turn-off delay time		-	65	130	ns
fall time		-	38	-	ns
Irain diode					
source-drain voltage	$I_S = -200 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C}$	-0.47	-0.88	-1.2	٧
	drain-source breakdown voltage gate-source threshold voltage drain leakage current gate leakage current gate leakage current drain-source on-state resistance forward transconductance characteristics total gate charge gate-source charge gate-drain charge input capacitance output capacitance reverse transfer capacitance turn-on delay time rise time turn-off delay time fall time	aracteristicsdrain-source breakdown voltage $I_D = -250 \ \mu A; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ gate-source threshold voltage $I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$ drain leakage current $V_{DS} = -30 \ V; \ V_{GS} = 0 \ V; \ T_j = 150 \ ^{\circ}C$ $V_{DS} = -30 \ V; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ gate leakage current $V_{GS} = 8 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{GS} = -8 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{GS} = -8 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{GS} = -4.5 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{GS} = -2.5 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{GS} = -2.5 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{GS} = -4.5 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{GS} = -4.5 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{GS} = -4.5 \ V; \ V_{DS} = 0 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{GS} = -4.5 \ V; \ V_{DS} = -10 \ mA; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = -10 \ V; \ I_D = -200 \ mA; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = -10 \ V; \ I_D = -200 \ mA; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = -15 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = -4.5 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = -4.5 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = -4.5 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = -4.5 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = -4.5 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = -4.5 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = -4.5 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = -4.5 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = -4.5 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = -4.5 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = -4.5 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = -4.5 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = -4.5 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = -4.5 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = -4.5 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = -4.5 \ V; \ T_j = 25 \ ^{\circ}C$ $V_{DS} = -4.5 \ V; \ $	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	drain-source breakdown voltage I _D = -250 μA; V _{GS} = 0 V; T _j = 25 °C -30	

30 V, 230 mA P-channel Trench MOSFET

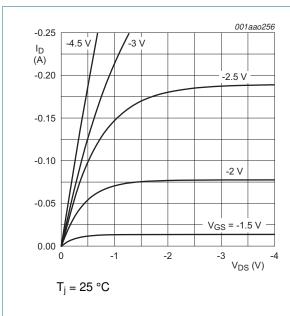
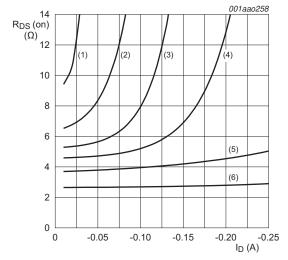


Fig 6. Output characteristics: drain current as a function of drain-source voltage; typical values



T_i = 25 °C

(1) $V_{GS} = -1.75 \text{ V}$

(2) $V_{GS} = -2.0 \text{ V}$

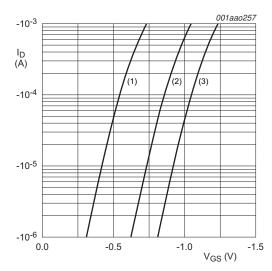
(3) $V_{GS} = -2.25 \text{ V}$

(4) $V_{GS} = -2.5 \text{ V}$

(5) $V_{GS} = -3.0 \text{ V}$

(6) $V_{GS} = -4.5 \text{ V}$

Fig 8. Drain-source on-state resistance as a function of drain current; typical values



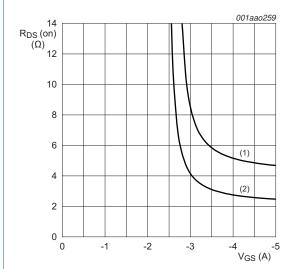
 $T_i = 25 \, ^{\circ}C; \, V_{DS} = -5 \, V$

(1) minimum values

(2) typical values

(3) maximum values

Fig 7. Sub-threshold drain current as a function of gate-source voltage



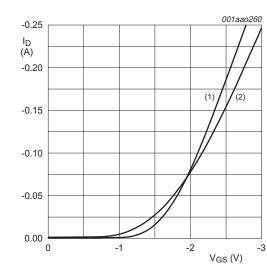
 $I_D = -200 \text{ mA}$

(1) $T_i = 150 \, ^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

Fig 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

30 V, 230 mA P-channel Trench MOSFET

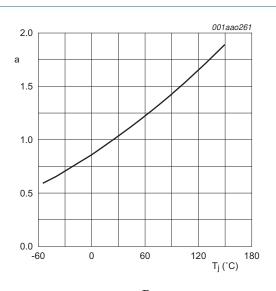


 $V_{DS} > I_D \times R_{DSon}$

(1)
$$T_i = 25 \, ^{\circ}C$$

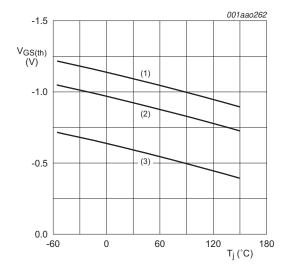
(2)
$$T_i = 150 \, ^{\circ}\text{C}$$

Fig 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

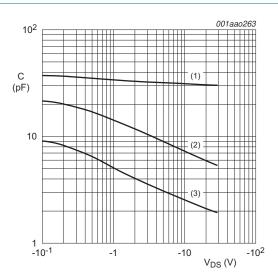
Fig 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values



 I_D = -0.25 mA; V_{DS} = V_{GS}

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig 12. Gate-source threshold voltage as a function of junction temperature



 $f = 1 \text{ MHz}; V_{GS} = 0 \text{ V}$

- (1)C_{iss}
- (2)C_{oss}
- (3)C_{rss}

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

30 V, 230 mA P-channel Trench MOSFET

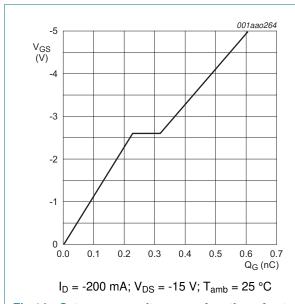


Fig 14. Gate-source voltage as a function of gate charge; typical values

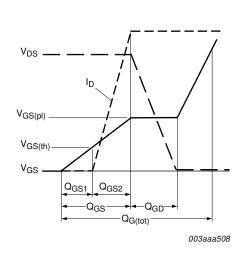
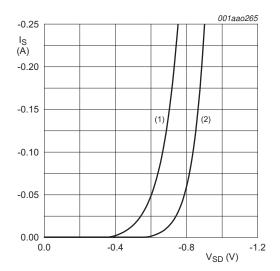


Fig 15. Gate charge waveform definitions



 $V_{GS} = 0 V$

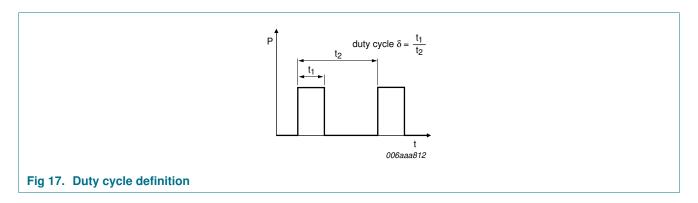
(1) $T_i = 150 \, ^{\circ}C$

(2) $T_j = 25 \, ^{\circ}C$

Fig 16. Source current as a function of source-drain voltage; typical values

30 V, 230 mA P-channel Trench MOSFET

8. Test information



8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline

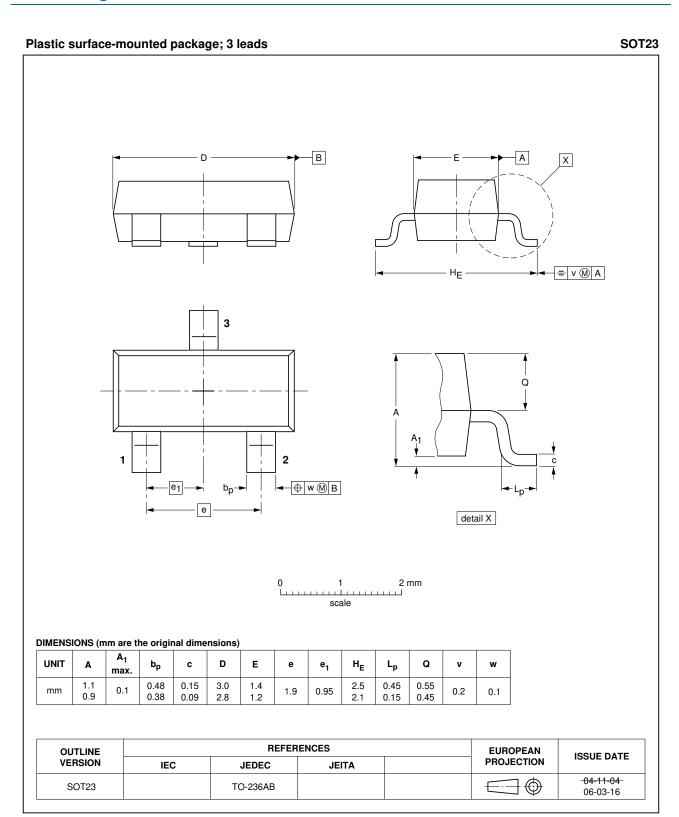
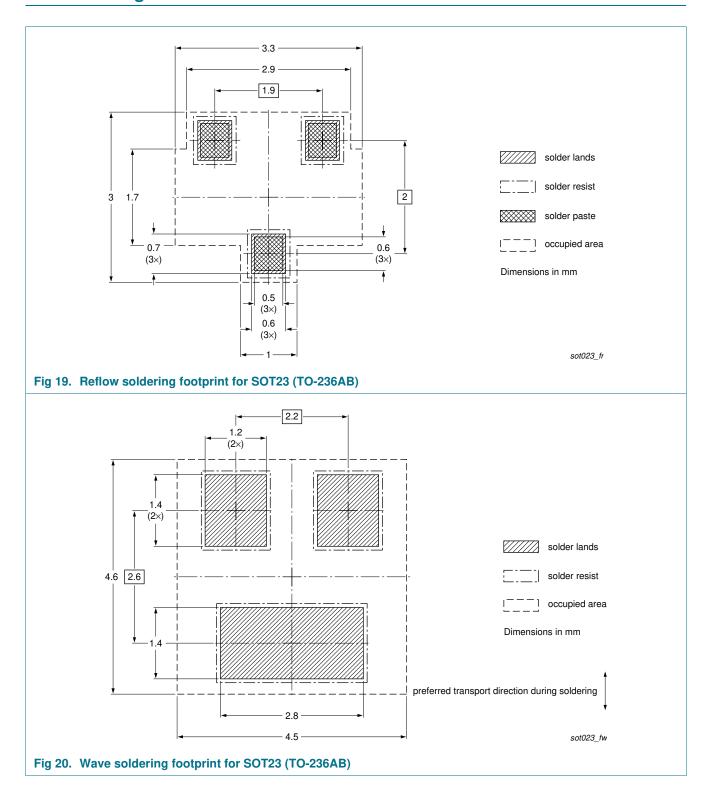


Fig 18. Package outline SOT23 (TO-236AB)

30 V, 230 mA P-channel Trench MOSFET

10. Soldering



30 V, 230 mA P-channel Trench MOSFET

11. Revision history

Table 8. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
NX3008PBK v.1	20110801	Product data sheet	-	-

30 V, 230 mA P-channel Trench MOSFET

12. Legal information

12.1 Data sheet status

Document status [1] [2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions".
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30 V, 230 mA P-channel Trench MOSFET

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